410x410um Silicon PD Chip datasheet

P/N : WS99-01A

Feature

Si PIN Photodiode chip

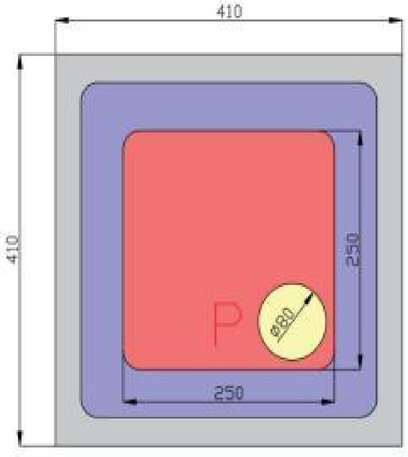
Structure

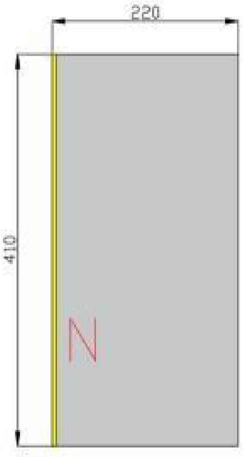
Planar type : PIN diode

Electrodes :

Back side (Cathode) : Au

Top side (Anode) : Al





DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	250± 10 x 250± 10			μm
Chip width	410			μm
Chip length	410			μm
Chip height	200	220	245	μm
Pad Area		80		μm

Electro-Optical Characteristics (@ Ta = 25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	30			V
Reverse Dark Current	Id	Vr=10V			10	nA
Sensitive Wavelength Range	λ		400	940	1100	nm
Capacitance	Cj	VR=3V, f=1MHz		2		pF